

Vishay Siliconix

Automotive P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	-60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.177			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.246			
I _D (A)	-2.8			
Configuration	Single			

FEATURES

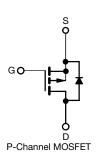
- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE





Marking Code: 9Dxxx

ORDERING INFROMATION			
Package	SOT-23		
Lead (Pb)-free and Halogen-free	SQ2361ES-T1-GE3		

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	-60	V	
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current	T _C = 25 °C	I _D	-2.8		
	T _C = 125 °C		-1.6		
Continuous Source Current (Diode Conduction)	I _S	-2.5	Α		
Pulsed Drain Current ^a	I _{DM}	-11			
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	-12.5		
Single Pulse Avalanche Energy	L = 0.1 111111	E _{AS}	7.8	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	р	2	W	
	T _C = 125 °C	P_{D}	0.67	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient P	CB Mount b	R_{thJA}	175	°C/W	
Junction-to-Foot (Drain)		R_{thJF}	75	C/VV	

Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. When mounted on 1" square PCB (FR4 material).



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-60	-	-	W
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = -250 \mu A$		-	-2.5	- V
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		V _{GS} = 0 V	V _{DS} = -60 V	-	-	-1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = -60 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	-	-	-50	μΑ
		$V_{GS} = 0 V$	$V_{DS} = -60 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$	-	-	-150	
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = -10 \text{ V}$	$V_{DS} \le -5 \text{ V}$	-10	-	-	Α
		V _{GS} = -10 V	I _D = -2.4 A	-	0.130	0.177	
Drain-Source On-State Resistance a	R _{DS(on)}	V _{GS} = -10 V	$I_D = -2.4 \text{ A}, T_J = 125 ^{\circ}\text{C}$	-	-	0.310	Ω
Brain Godice on State Nesistance	D3(0H)	V _{GS} = -10 V	$I_D = -2.4 \text{ A}, T_J = 175 \text{ °C}$	-	-	0.320	
		$V_{GS} = -4.5 \text{ V}$	I _D = -1.8 A	-	0.205	0.246	
Forward Transconductance b	9 _{fs}	V _{DS} :	$V_{DS} = -10 \text{ V}, I_{D} = -2 \text{ A}$		5	-	S
Dynamic ^b	_	_					1
Input Capacitance	C _{iss}			-	380	550	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{GS} = 0 V$ $V_{DS} = -30 V, f = 1 MHz$	-	50	75	pF
Reverse Transfer Capacitance	C _{rss}			-	30	42	
Total Gate Charge ^c	Qg			-	9	12	
Gate-Source Charge c	Q _{gs}	V _{GS} = -10 V	$V_{DS} = -30 \text{ V}, I_{D} = -6 \text{ A}$	-	1.6	-	nC
Gate-Drain Charge ^c	Q _{gd}	1		-	3.3	_	
Gate Resistance	Rg		f = 1 MHz		4.1	5.2	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	8	11	
Rise Time ^c	t _r	V_{DD} = -30 V, R_L = 20 Ω $I_D \cong$ -1.5 A, V_{GEN} = -10 V, R_g = 1 Ω		-	9	12	- ns
Turn-Off Delay Time ^c	t _{d(off)}			-	22	26	
Fall Time °	t _f			-	4	6	
Source-Drain Diode Ratings and Chara	cteristics b						
Pulsed Current a	I _{SM}			-	-	-11	Α
Forward Voltage	V _{SD}	I _F = -1.5 A, V _{GS} = 0 V			-0.9	-1.2	V

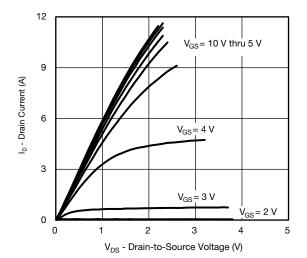
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

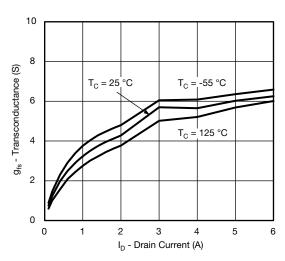
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



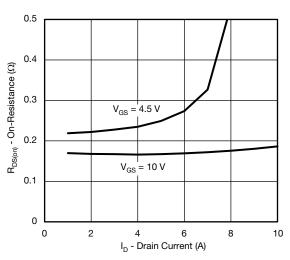
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



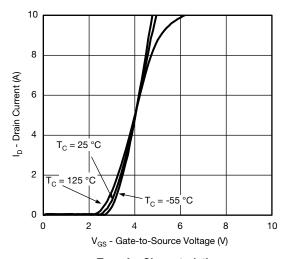
Output Characteristics



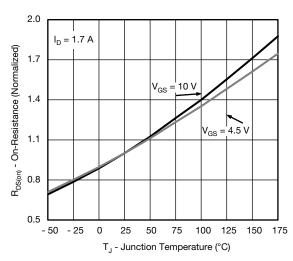
Transconductance



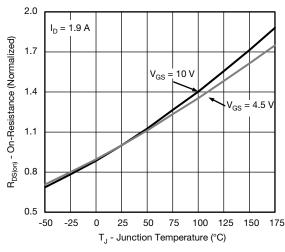
On-Resistance vs. Drain Current



Transfer Characteristics



On-Resistance vs. Junction Temperature

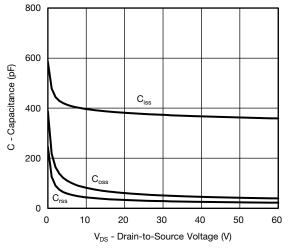


On-Resistance vs. Junction Temperature

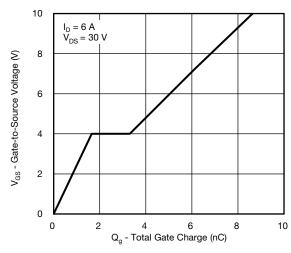
For technical questions, contact: automoste



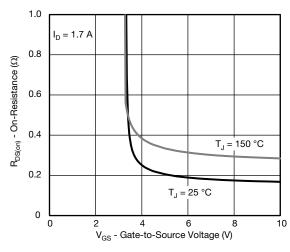
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



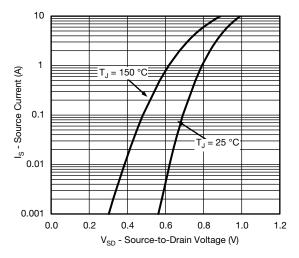
Capacitance



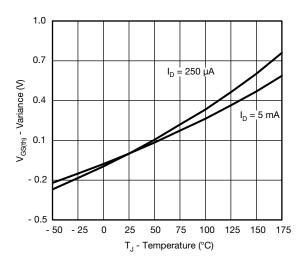
Gate Charge



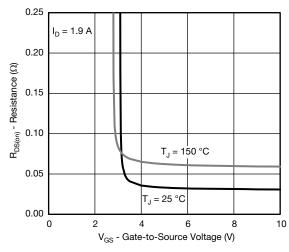
On-Resistance vs. Gate-Source Voltage



Source-Drain Diode Forward Voltage



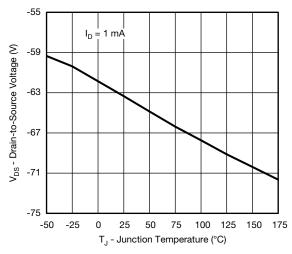
Threshold Voltage

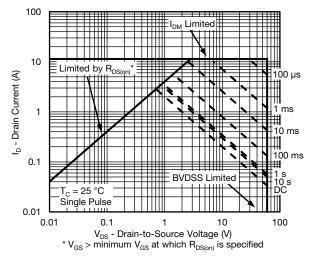


On-Resistance vs. Gate-Source Voltage



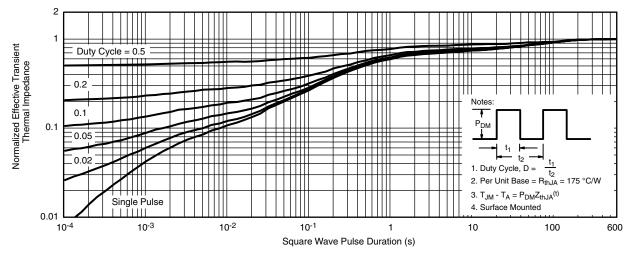
THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)





Drain-Source Breakdown vs. Junction Temperature

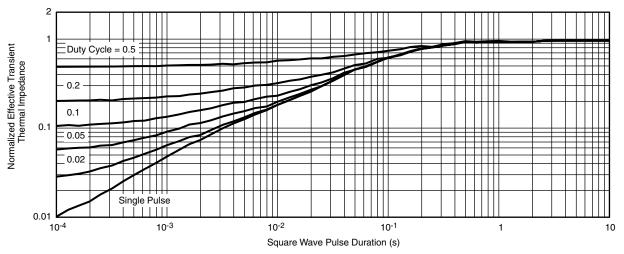
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg266894.

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SOT-23 (TO-236): 3-LEAD







Dim	MILLI	METERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.074	8 Ref	
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
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RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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